

Vishay Semiconductors

### 2 Form A Solid State Relay

#### Features

- Load Voltage, 15 V
- Load Current, 150 mA
- Isolation Test Voltage 5300 V<sub>RMS</sub>
- Switching Capability up to 50 MHz
- · Blocking Capability Dependent upon Signal dv/dt
- Low and Typical R<sub>ON</sub> 5.0  $\Omega$
- 1.0 ms Actuation Time
- Low Power Consumption
- · Balanced Switching
- Clean, Bounce-free Switching
- Surface-mountable
- · Lead-free component
- Component in accordance to RoHS 2002/95/EC and WEEE 2002/96/EC

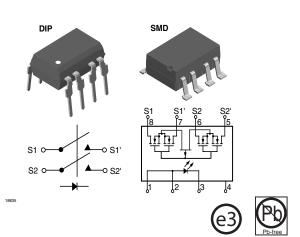
#### **Agency Approvals**

- UL1577, File No. E52744 System Code H or J, Double Protection
- CSA Certification 093751
- DIN EN 60747-5-2 (VDE0884) DIN EN 60747-5-5 pending

#### **Applications**

- Protection Switching (T1 sparing)
- Digital Access Cross Connects
- D-type Channel Breaks
- Intraoffice Data Routing
- **Transmission Switching**
- T1 Multiplexing
- DSO (64 Kbit/s)
- DS1 (1.544 Mbit/s)
- E1, DS1A (2.048 Mbit/s)
- DS1C (3.152 Mbit/s)
- DS2 (6.312 Mbit/s)
- Instrumentation
- Scanners
- Testers
- Measurement Equipment

See T1 Switching with the LH1514 Solid State Relay (Appnote 67)



#### Description

The LH1514 is a DPST normally open (2 Form A) SSR that can be used in balanced high-frequency applications like T1 switching. With its low ON-resistance and high actuation rate, the LH1514 is also very attractive as a general-purpose 2 Form A SSR for balanced signals.

The relays are constructed using a GaAIAs LED for actuation control and an integrated monolithic die for the switch output. The die, fabricated in a dielectrically isolated Smart Power BiCMOS, is comprised of a photodiode array, switch control circuitry, and NMOS switches.

In balanced switching applications, internal circuitry shunts high-frequency signals between two poles when the SSR is off. This balanced T termination technique provides high isolation for the load.

#### **Order Information**

Part	Remarks
LH1514AAC	Gullwing, Tubes, SMD-8
LH1514AACTR	Gullwing, Tape and Reel, SMD-8
LH1514AB	Tubes, DIP-8



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Absolute Maximum Ratings, T<sub>amb</sub> = 25 °C Stresses in excess of the absolute Maximum Ratings can cause permanent damage to the device. Functional operation of the device is not implied at these or any other conditions in excess of those given in the operational sections of this document. Exposure to absolute Maximum Ratings for extended periods of time can adversely affect reliability.

#### SSR

Parameter	Test condition	Symbol	Value	Unit
LED input ratings: continuous forward current		l <sub>F</sub>	50	mA
LED input ratings: reverse voltage	I <sub>R</sub> ≤ 10 μA	V <sub>R</sub>	10	V
Output operation: dc or peak ac load voltage	I <sub>L</sub> ≤ 1.0 μA	VL	15	V
Output operation: continuous dc load current, each pole, two poles operating simultaneously		ΙL	150	mA
Ambient operating temperature range		T <sub>amb</sub>	- 40 to + 85	°C
Storage temperature range		T <sub>stg</sub>	- 40 to + 150	°C
Pin soldering temperature	t = 10 s max	T <sub>sld</sub>	260	°C
Input/output isolation voltage		V <sub>ISO</sub>	5300	V <sub>RMS</sub>
Power dissipation		P <sub>diss</sub>	600	mW

### Electrical Characteristics, $T_{amb} = 25 \ ^{\circ}C$

Minimum and maximum values are testing requirements. Typical values are characteristics of the device and are the result of engineering evaluations. Typical values are for information only and are not part of the testing requirements.

#### Input

Parameter	Test condition	Symbol	Min	Тур.	Max	Unit
LED forward current, switch turn-on	I <sub>L</sub> = 100 mA, t = 10 ms	I <sub>Fon</sub>		2.0	3.0	mA
LED forward current, switch turn-off	$V_L = \pm 10 V$	I <sub>Foff</sub>	0.2	1.8		mA
LED Forward voltage	I <sub>F</sub> = 10 mA	V <sub>F</sub>	1.15	1.26	1.45	V



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#### Output

Parameter	Test condition	Symbol	Min	Тур.	Max	Unit
ON-resistance	$I_{F} = 10 \text{ mA}, I_{L} = \pm 50 \text{ mA}$	R <sub>ON</sub>	2.0	3.0	5.0	Ω
Pole-to-pole ON-resistance matching (S1 to S2)	$I_{F} = 10 \text{ mA}, I_{L} = \pm 50 \text{ mA}$			0.2	1.0	DΩ
Output off-state bleed-through <sup>1)</sup>	f = 1.5 MHz square wave t <sub>r</sub> /t <sub>f</sub> = 5.0 ns (see Figure 13.)			70	100	mV <sub>peak</sub>
Output off-state leakage	$I_{F} = 0 \text{ mA}, V_{L} = \pm 5.0 \text{ V}$	Ι <sub>Ο</sub>		3 × 10 <sup>-12</sup>	200 × 10 <sup>-9</sup>	А
	$I_{F} = 0 \text{ mA}, V_{L} = \pm 15 \text{ V}$	Ι <sub>Ο</sub>		20 × 10 <sup>-12</sup>	1.0 × 10 <sup>-6</sup>	А
Output off-state leakage pole-to-pole	I <sub>F</sub> = 10 mA, Pins 7, 8 ± 3.0 V, Pins 5, 6 Gnd	Ι <sub>Ο</sub>		1.0	5.0	μA
	Pins 7, 8 ± 15 V, Pins 5, 6 Gnd	۱ <sub>0</sub>		2.0	50	μA
Output capacitance Pins 5 to 6, 7 to 8	$I_{F} = 0 \text{ mA}, V_{L} = 0 \text{ V}$	C <sub>O</sub>		20		pF
Pole-to-pole capacitance (S1 to S2)	$I_{F} = 0 \text{ mA}, V_{L} = 0 \text{ V}$			20		pF
	$I_{F} = 10 \text{ mA}, V_{L} = 0 \text{ V}$			50		pF

<sup>1)</sup> Guaranteed by component measurement during wafer probe.

#### Transfer

Parameter	Test condition	Symbol	Min	Тур.	Max	Unit
Turn-on time	$I_{F} = 10 \text{ mA}, I_{L} = 20 \text{ mA}$	t <sub>on</sub>		0.4	1.0	ms
Turn-off time	I <sub>F</sub> = 10 mA, I <sub>L</sub> = 20 mA	t <sub>off</sub>		0.6	1.0	ms

#### **Recommended Operating Conditions**

Parameter	Test condition	Symbol	Min	Тур.	Max	Unit
LED forward current for switch turn-on	$T_{amb} = -40 \text{ °C to} + 85 \text{ °C}$	I <sub>Fon</sub>	10		20	mA

#### Typical Characteristics (Tamb = 25 °C unless otherwise specified)

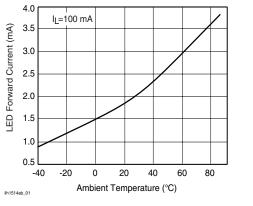


Figure 1. LED Forward Current for Switch Turn-on/off

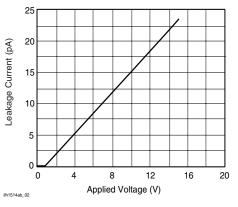


Figure 2. Leakage Current vs. Applied Voltage

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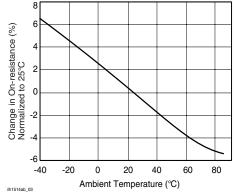


Figure 3. ON-Resistance vs. Temperature

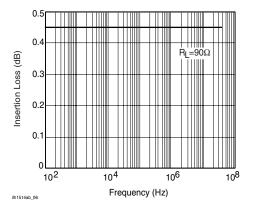


Figure 6. Insertion Loss (per Pole) vs. Frequency

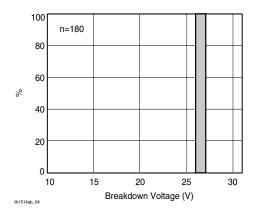
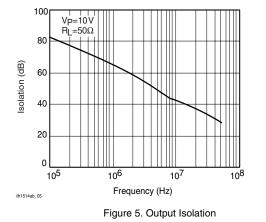


Figure 4. Breakdown Voltage Distribution Typical



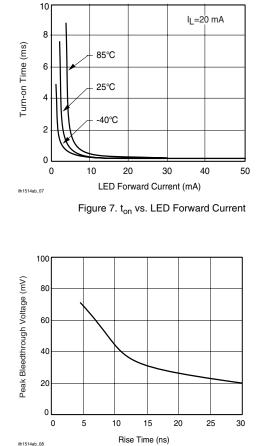
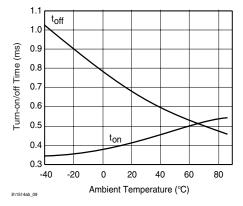


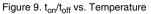
Figure 8. Bleed-through Voltage vs. Rise Time

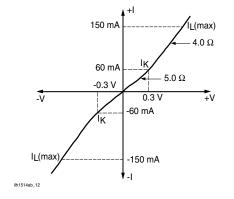
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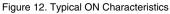


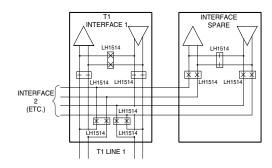
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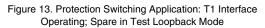


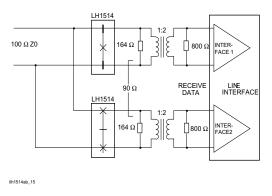






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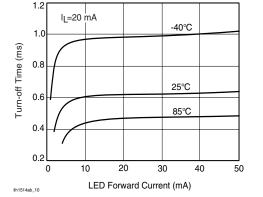
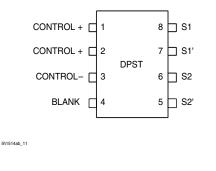
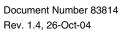


Figure 10.  $t_{\text{off}}$  vs. LED Forward Current

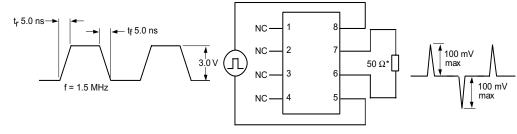






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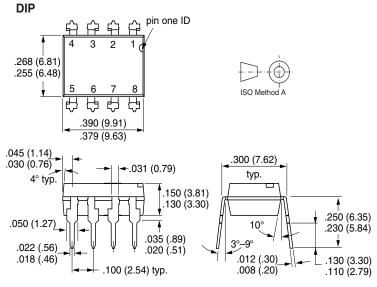




\* 50  $\Omega$  load is derived from T1 applications where a 100  $\Omega$  load is paralleled with a 100  $\Omega$  line.  $_{\text{intS14ab,13}}$ 

Figure 15. Off-state Bleed-through

#### Package Dimensions in Inches (mm)



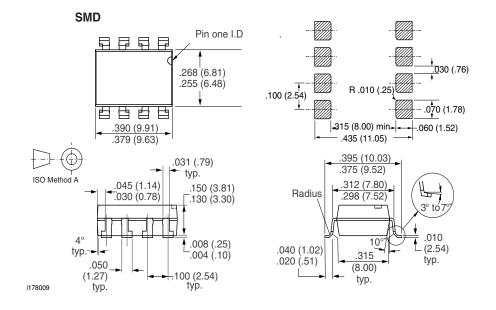
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**Vishay Semiconductors** 

#### Package Dimensions in Inches (mm)



#### **Vishay Semiconductors**



#### **Ozone Depleting Substances Policy Statement**

It is the policy of Vishay Semiconductor GmbH to

- 1. Meet all present and future national and international statutory requirements.
- 2. Regularly and continuously improve the performance of our products, processes, distribution and operatingsystems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) intend to severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

Vishay Semiconductor GmbH has been able to use its policy of continuous improvements to eliminate the use of ODSs listed in the following documents.

- 1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively
- 2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA
- 3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

Vishay Semiconductor GmbH can certify that our semiconductors are not manufactured with ozone depleting substances and do not contain such substances.

We reserve the right to make changes to improve technical design and may do so without further notice.

Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer. Should the buyer use Vishay Semiconductors products for any unintended or unauthorized application, the buyer shall indemnify Vishay Semiconductors against all claims, costs, damages, and expenses, arising out of, directly or indirectly, any claim of personal damage, injury or death associated with such unintended or unauthorized use.

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